

INFORMATION DISCLOSURE
CITATION

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925-179

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APPLICANT

NAGAHAMA et al

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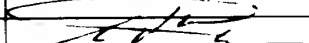
U.S. PATENT DOCUMENTS

[illegible]

FOREIGN PATENT DOCUMENTS

FOREIGN PATENT DOCUMENTS							TRANSLATION	
DOCUMENT		DATE	COUNTRY	CLASS	SUBCLASS	YES	NO	
W3L ↓	09321338A	12/1997	Japan			Abstract		
	5-243614	9/1993	Japan				X	
	9-83016	3/1997	Japan				X	
	EP 0 874 405	10/1998	Europe			X		
	8-64791	3/1996	Japan				X	

OTHER DOCUMENTS (including Author, Title, Date, Pertinent pages, etc.)

W56-	Nakamura et al: "High-power, Long-Lifetime InGaN/GaN/AlGaIn-Based Laser Diodes Grown on Pure GaN Substrates," <i>Jpn J. Appl. Phys.</i> , Vol. 37 (1998) pp. 309-312		
*Examiner		Date Considered	7/18/02

Examiner: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to application.